

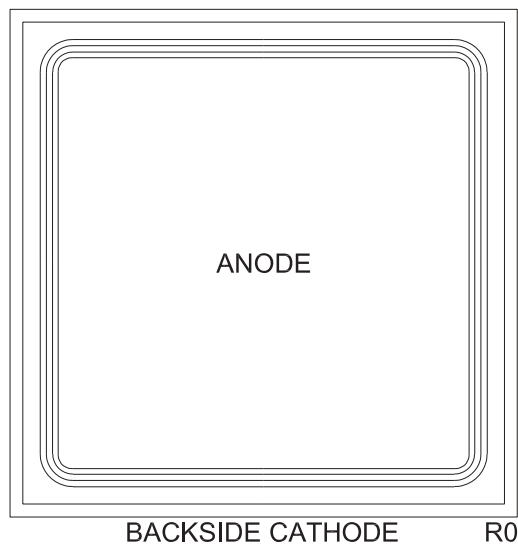
PROCESS CPD85V
Schottky Rectifier
1 Amp Schottky Barrier Rectifier Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	39.4 x 39.4 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	35 x 35 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



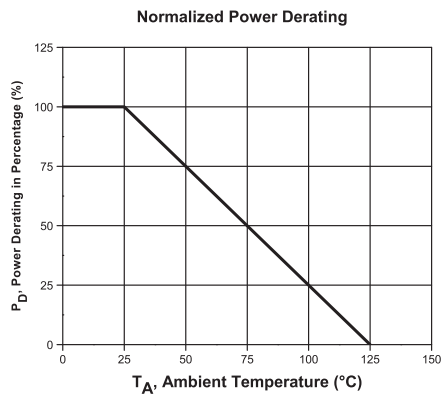
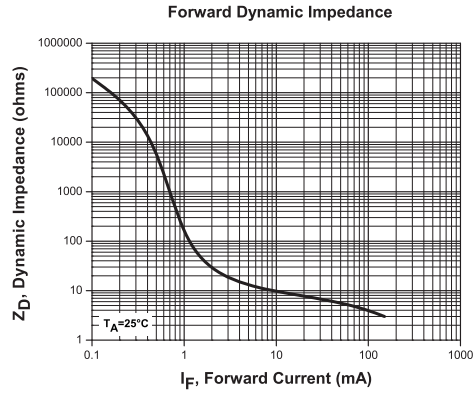
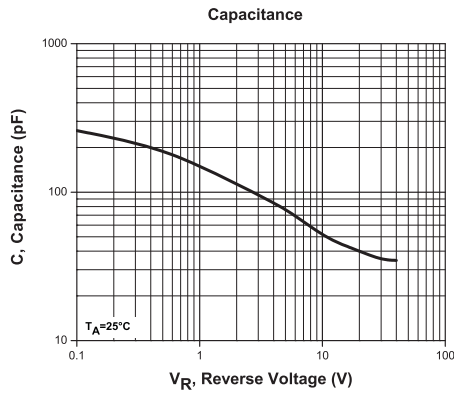
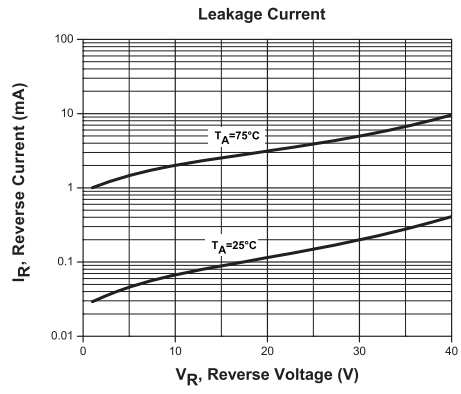
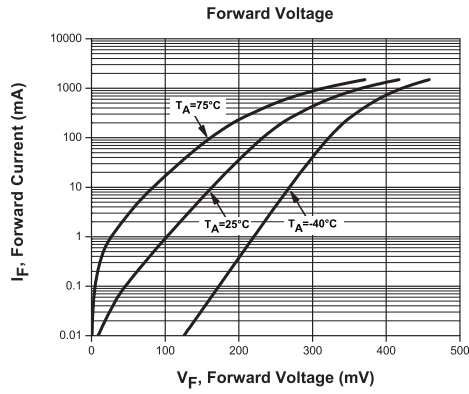
GROSS DIE PER 5 INCH WAFER
10,900

PRINCIPAL DEVICE TYPES
CMPSH1-4L

R1 (22-March 2010)

PROCESS CPD85V

Typical Electrical Characteristics



R1 (22-March 2010)